



DCR1840Y85

Phase Control Thyristor

Replaces DS5767-3 DS5767-4 March 2023 (LN42480)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
		$T_{vj} = -40^{\circ}C$ to 125°C,
DCR1840Y85*	8500	IDRM = IRRM = 300mA,
DCR1840Y80	8000	VDRM, VRRM tp = 10ms
DCR1840Y75	7500	VDSM & VRSM =
DCR1840Y70	7000	VDRM & VRRM + 100V
		respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1840Y85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

\mathbf{V}_{DRM}	8500V
I _{T(AV)}	1830A
Ітѕм	25000A
dV/dt*	1500V/μs
dl/dt	300A/μs

^{*} Higher dV/dt selections are available on request

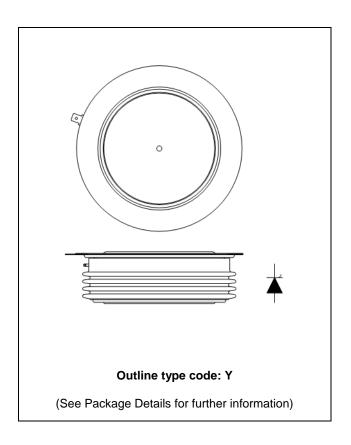


Fig. 1 Package outline

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^{*8200}V @ -40°C, 8500V @ 0°C



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
İT(AV)	Mean on-state current	Half wave resistive load	1830	А
It(RMS)	RMS value	-	2870	А
lτ	Continuous (direct) on-state current	-	2750	Α

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	25.0	kA
l²t	I ² t for fusing	V _R = 0	3.13	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
		Double side cooled	DC	-	8.4	°C/kW
Rth(j-c)	Rth(j-c) Thermal resistance - junction to case	Single side cooled	Anode DC	-	13.4	°C/kW
			Cathode DC	-	23.1	°C/kW
D. C.	Rth(c-h) Thermal resistance - case to heatsink	Clamping force 54kN	Double side	-	2.0	°C/kW
Kth(c-h)		(with mounting compound)	Single side	-	4.0	°C/kW
Tvj	Virtual junction temperature Blocking VDRM / VRRM			-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			48	59	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	300	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		3.10	3.50	٧
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)} Gate source 30V, 10Ω	Repetitive 50Hz	-	150	A/µs
ui/at	ivate of fise of off-state current	tr < 0.5µs, Tj = 125°C	Non-repetitive	-	300	A/µs
V	Threshold voltage - Low level	500A to 1500A at Tcase = 125°C		-	1.04	٧
V T(TO)	Threshold voltage - High level	1500A to 7000A at Tcase = 125°C		-	1.29	V
	On-state slope resistance - low level	500A to 1500A at Tcase = 125°C		-	0.72	mΩ
ľτ	On-state slope resistance - High level	1500A to 7000A at Tcase = 125°C		-	0.55	mΩ
tgd	Delay time	$V_D = 67\%$ VDRM, gate source 30V, 10Ω tr = 0.5 μ s, Tj = 25°C		-	3	μs
tq	Turn-off time	T _j = 125°C, V _R = 200V, dl/dt = 1A/μs, dV _{DR} /dt = 20V/μs linear		-	1200	μs
Qs	Stored charge	Iτ = 2000A, T _j = 125°C, dI/dt = 1A/μs VR(peak) ~ 5100V, VRM ~ 3400V		4920	7040	μC
IRR	Reverse recovery current			51	63	А
lι	Latching current	Tj = 25°C, VD = 5V		-	3	Α
Ін	Holding current	$T_{j} = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_{T} = 5A$		-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
V GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Ідт	Gate trigger current	VDRM = 5V, Tcase = 25°C	400	mA
lgp	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	15	mA

CURVES

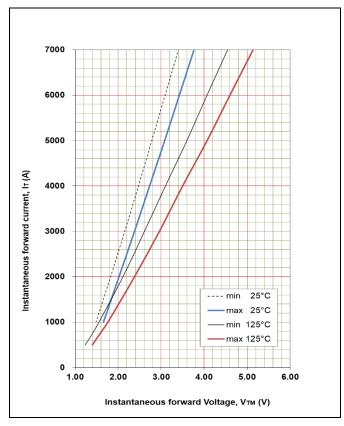


Fig. 2 Maximum & minimum on state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.525462

B = 0.077304

C = 0.000479

D = 0.006921

These values are valid for $T_j = 125^{\circ}C$ for I_{T} 500A to 7000A

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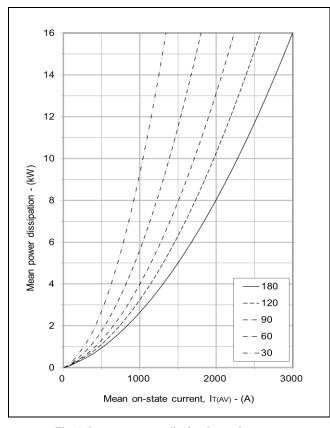


Fig. 3 On-state power dissipation - sine wave

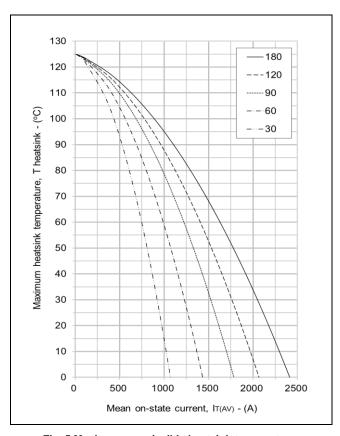


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

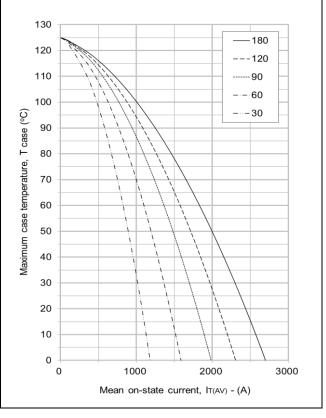


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

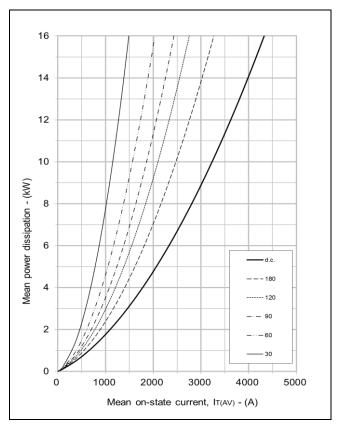


Fig. 6 On-state power dissipation - rectangular wave

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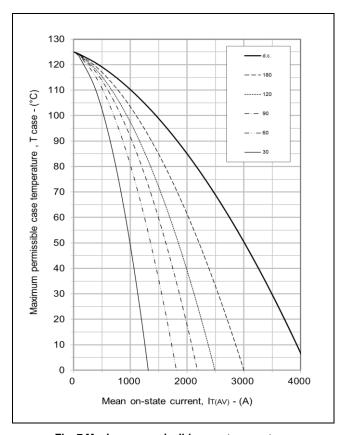
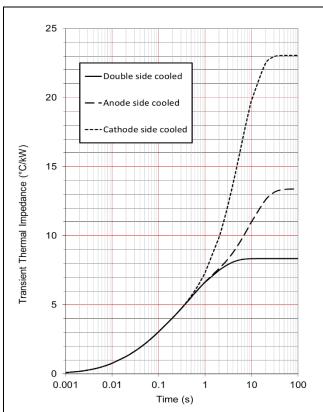


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



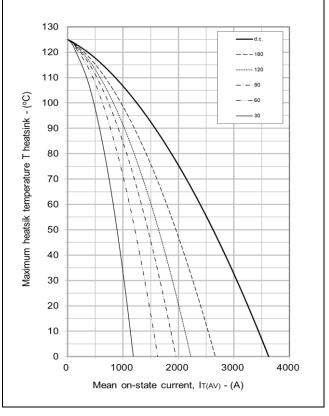


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	0.612	1.772	3.105	2.861
cooled	Ti(s)	0.010	0.056	0.333	1.632
Anode side cooled	Ri(°C/kW)	0.701	1.939	3.610	7.138
	Ti(s)	0.011	0.066	0.420	9.061
Cathode side cooled	Ri(°C/kW)	0.673	2.017	1.731	18.639
	Ti(s)	0.011	0.066	0.304	5.727

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th}(j-c)}$ when the device operates at conduction angles other than d.c.

D	Double side cooling				
	ΔZ_{th}	(Z)			
θ°	sine.	rect.			
180	0.94	0.65			
120	1.09	0.92			
90	1.24	1.07			
60	1.38	1.23			
30	1.49	1.40			
15	1.54	1 10			

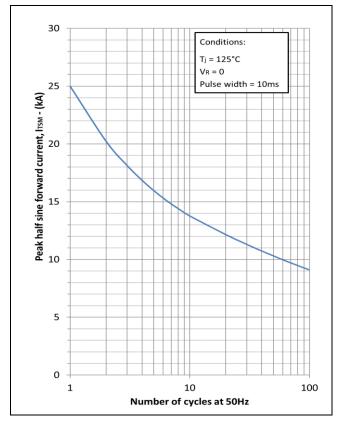
Ar	node Side Cooling			
	ΔZ_t	_h (Z)		
θ°	sine.	rect.		
180	0.94	0.64		
120	1.08	0.91		
90	1.23	1.06		
60	1.37	1.22		
30	1.47	1.38		

Cath	ode Sided Cooling			
	ΔZ_t	h (Z)		
θ°	sine.	rect.		
180	0.94	0.64		
120	1.08	0.91		
90	1.24	1.06		
60	1.37	1.22		
30	1.48	1.39		
15	1.53	1 48		

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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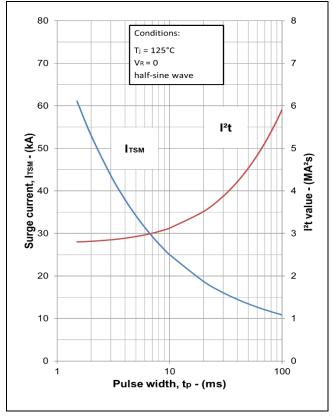


Fig. 10 Multi-cycle surge current

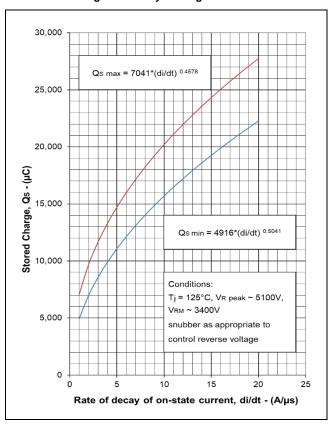


Fig. 12 Stored charge

Fig. 11 Single-cycle surge current

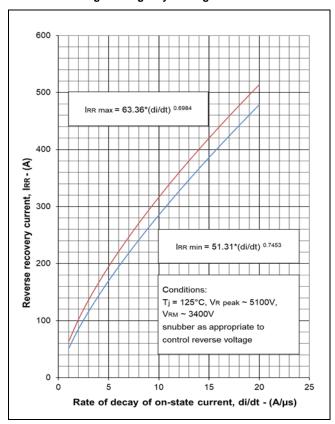


Fig. 13 Reverse recovery current

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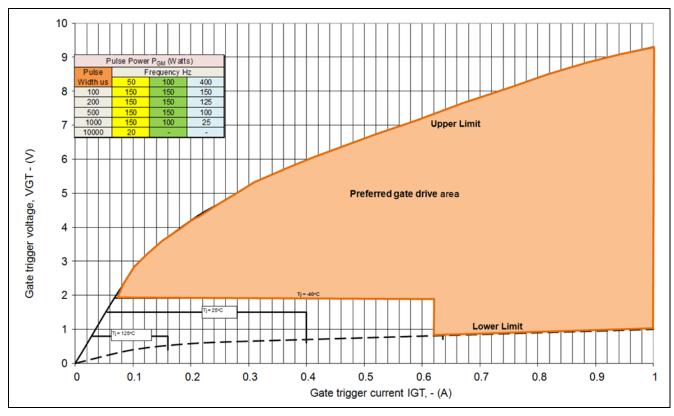


Fig. 14 Gate characteristics

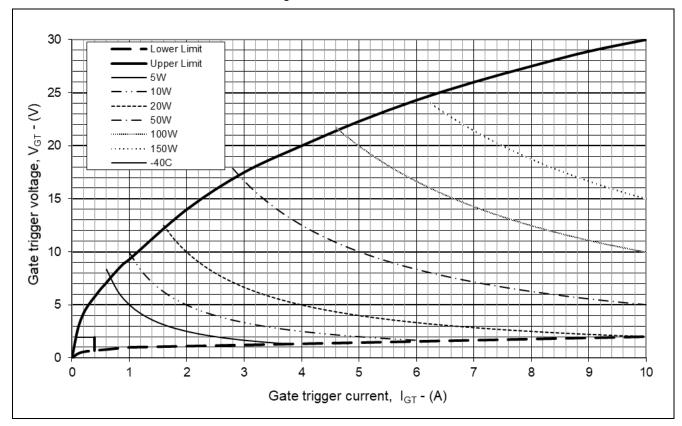


Fig. 15 Gate characteristics

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PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

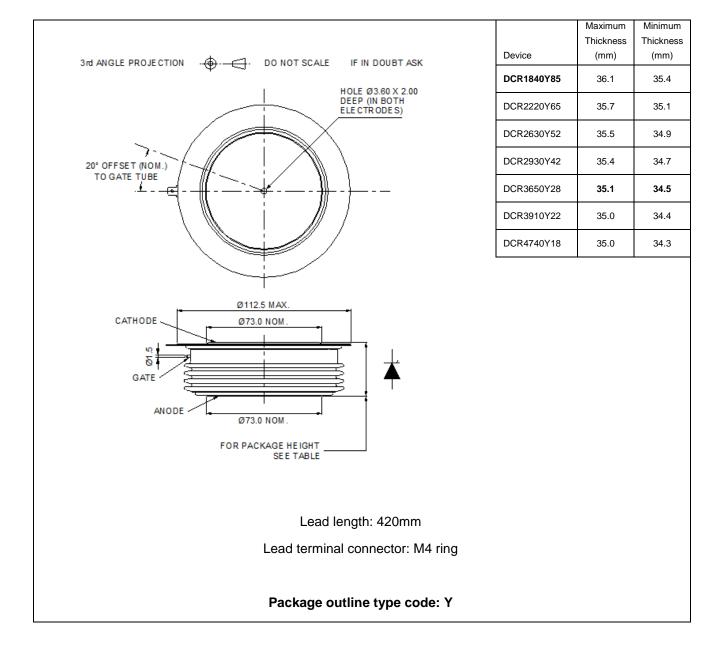


Fig. 16 Package outline

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